

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

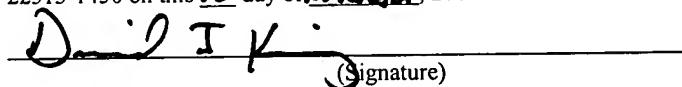


First Named Inventor:	John P. Snyder	Confirmation No.:	1961
Application No.:	10/796,514	Examiner:	Kim, Su C
Filing Date:	03/09/2004	Group Art Unit:	2823
Title:	TRANSISTOR HAVING HIGH DIELECTRIC GATE INSULATING LAYER AND SOURCE AND DRAIN FORMING SCHOTTKY CONTACT WITH SUBSTRATE		

RESPONSE AFTER FINAL UNDER 37 C.F.R. 1.116

Mail Stop AF
 Commissioner for Patents
 P.O. Box 1450
 Alexandria, Virginia 22313-1450

I hereby certify that this document is being sent via First Class U.S. mail addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on this 13 day of November, 2007.


 (Signature)

Dear Sir:

Applicant hereby submits a response to the Final Office Action dated June 11, 2007.

Claims are reflected in the listing of claims which begins on page 2 of this paper. Claims 1, 15, 24, 33, 44 and 55 have been amended to patentably distinguish the present invention over the cited prior art.

Remarks/Arguments begin on page 11 of this paper.